Digital Transistors (BRT) R1 = 10 k\Omega, R2 = 47 k Ω

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	۱ _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

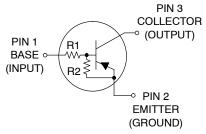
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

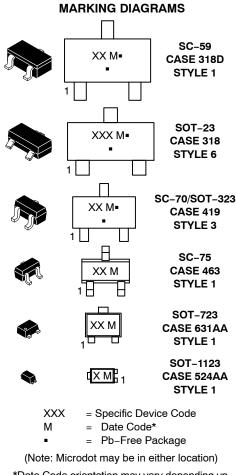


ON Semiconductor®

www.onsemi.com







*Date Code orientation may vary depending upon manufacturing location.

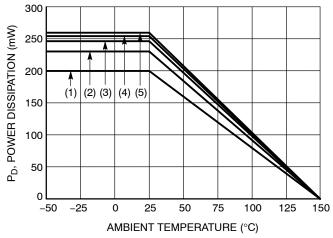
ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2114T1G, SMUN2114T1G*	6D	SC-59	3,000 / Tape & Reel
MMUN2114LT1G, SMMUN2114LT1G*	A6D	SOT-23	3,000 / Tape & Reel
MMUN2114LT3G, NSVMMUN2114LT3G*	A6D	SOT-23	10,000 / Tape & Reel
MUN5114T1G, SMUN5114T1G*	6D	SC-70/SOT-323	3,000 / Tape & Reel
SMUN5114T3G	6D	SC-70/SOT-323	10,000 / Tape & Reel
DTA114YET1G, SDTA114YET1G*	6D	SC-75	3,000 / Tape & Reel
DTA114YM3T5G, NSVDTA114YM3T5G*	6D	SOT-723	8,000 / Tape & Reel
NSBA114YF3T5G	К	SOT-1123	8,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SC-75 and SC-70/SOT-323; Minimum Pad
 SC-59; Minimum Pad
 SOT-23; Minimum Pad
 SOT-1123; 100 mm², 1 oz. copper trace
 SOT-723; Minimum Pad

Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2114)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1)	P _D	230 338 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 1) (Note 2)	R_{\thetaJA}	2.7 540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2114L)		-		
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	PD	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5114)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTA114YE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	600 400	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTA114YM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	480 205	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

FR-4 @ Minimum Pad.
 FR-4 @ 1.0 x 1.0 Inch Pad.
 FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
THERMAL CHARACTERISTICS (SOT-1123) (NSBA114YF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	PD	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ ext{ heta}JL}$	193	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	–55 to +150	°C

1. FR-4 @ Minimum Pad. 2. FR-4 @ 1.0 x 1.0 Inch Pad.

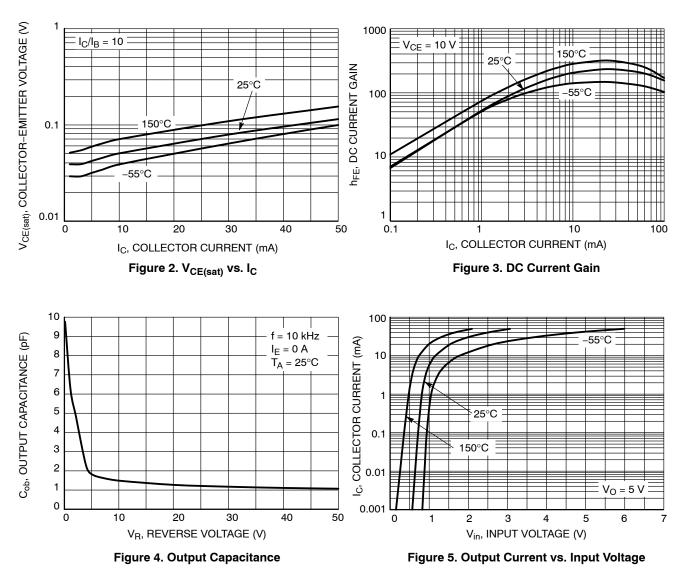
3. FR-4 @ 100 mm², 1 oz. copper traces, still air. 4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	-	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	_	_	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I _{EBO}	_	-	0.2	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V _(BR) CBO	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V _{(BR)CEO}	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) $(I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V})$	h _{FE}	80	140	-	
Collector – Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$	V _{CE(sat)}	-	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_C = 100 \ \mu\text{A})$	V _{i(off)}	-	0.7	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.2 \text{ V}, I_C = 1.0 \text{ mA})$	V _{i(on)}	1.4	0.9	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R ₁ /R ₂	0.17	0.21	0.25	

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



TYPICAL CHARACTERISTICS MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3

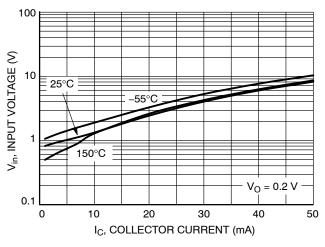
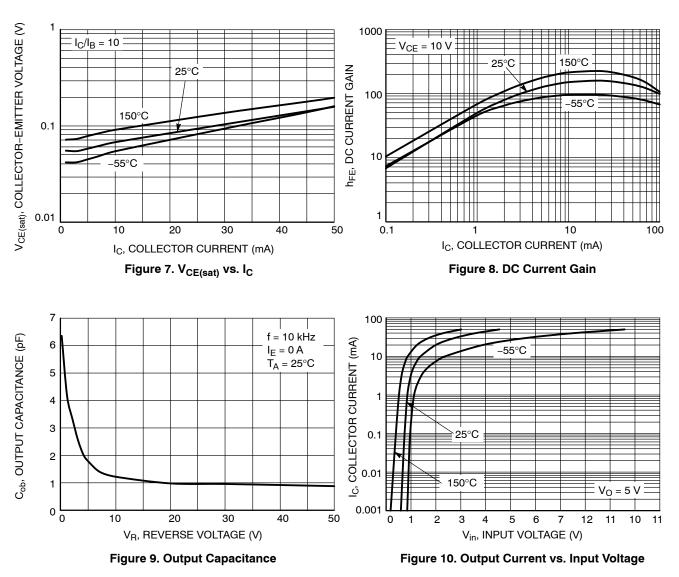


Figure 6. Input Voltage vs. Output Current



TYPICAL CHARACTERISTICS NSBA114YF3

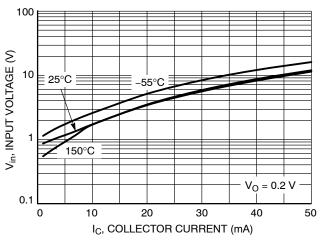


Figure 11. Input Voltage vs. Output Current

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

onsemi



SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

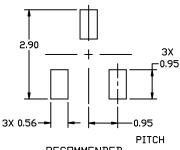
END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED 0	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserve the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particula purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitatio special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.			

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

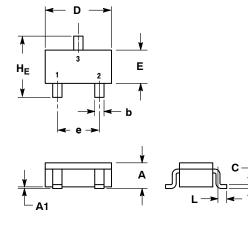
onsemi and ONSEMi. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

DUSEU



SC-59 CASE 318D-04 **ISSUE H**

DATE 28 JUN 2012



GENERIC **MARKING DIAGRAM***



XXX	= Specific Device Code
М	= Date Code
	= Pb-Free Package*

= Pb-Free Package*

(*Note: Microdot may be in either location)

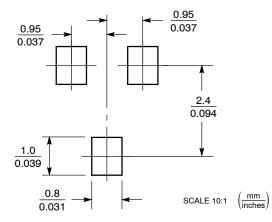
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

DIRES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
Ш	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
Г	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118



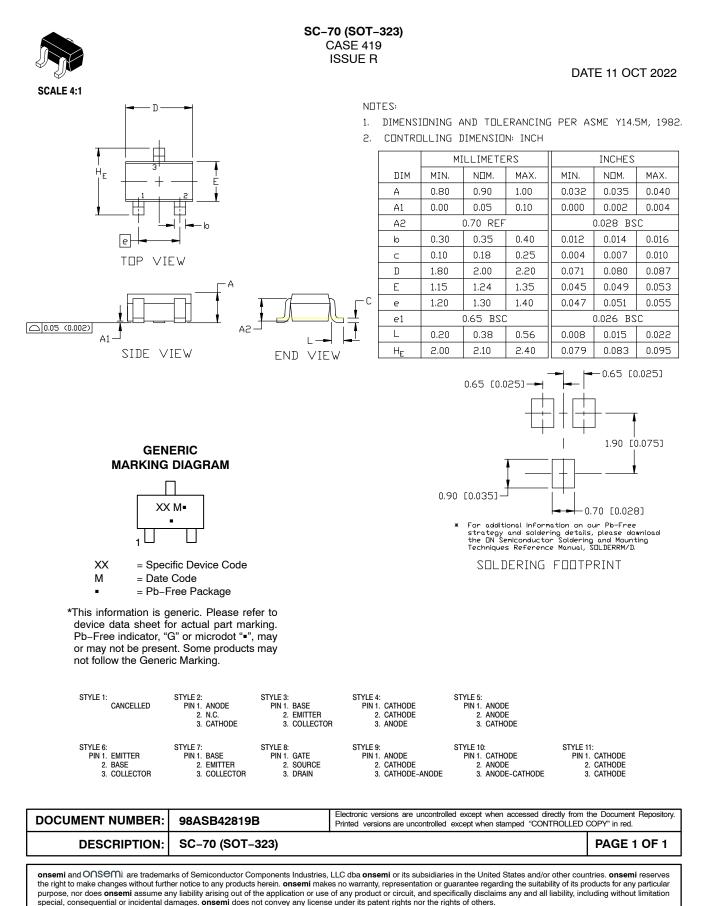


*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE
2. EMITTER	2. N.C.	2. ANODE
COLLECTOR	3. CATHODE	3. CATHODE
STYLE 4: PIN 1. CATHODE 2. N.C. 3. ANODE	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42664B Electronic versions are uncontrolled except when accessed directly from the Document Repositor. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SC-59		PAGE 1 OF 1		
onsemi and ONSEMI: are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.					

onsemi



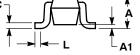
onsemi

DATE 07 AUG 2015



ISSUE G SCALE 4:1 -E--De ¥ b 3 PL 🕀 0.20 (0.008) 🛞 D H_{E} 0.20 (0.008) E _ С

SC-75/SOT-416 **CASE 463**



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR



3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

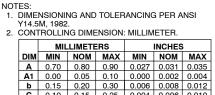
STYLE 5: PIN 1. GATE 2 SOURCE 3. DRAIN

GENERIC **MARKING DIAGRAM***



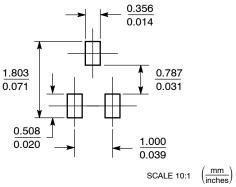
- XX = Specific Device Code
- Μ = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
Е	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC		0.04 BSC			
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

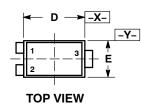
DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

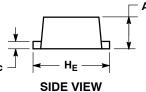
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

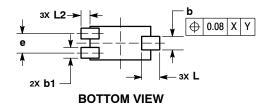
onsemí



SCALE 8:1







SOT-1123 CASE 524AA ISSUE C

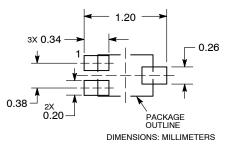
DATE 29 NOV 2011

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME

- Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN MAX			
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
С	0.07	0.17		
D	0.75	0.85		
Е	0.55	0.65		
е	0.35 0.40			
HE	0.95 1.05			
Ĺ	0.185 REF			
L2	0.05	0.15		

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 5: PIN 1. GATE

2. SOURCE 3. DRAIN

GENERIC MARKING DIAGRAM*



X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE
3. COLLECTOR	CATHODE	3. CATHODE	3. ANODE

 DOCUMENT NUMBER:
 98AON23134D
 Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

 DESCRIPTION:
 SOT-1123, 3-LEAD, 1.0x0.6x0.37, 0.35P
 PAGE 1 OF 1

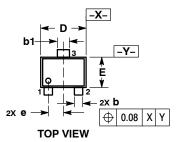
 onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular

the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights of others.

DUSEU



SCALE 4:1



GENERIC

MARKING DIAGRAM*

XX M

= Date Code

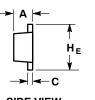
not follow the Generic Marking.

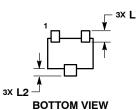
*This information is generic. Please refer to

device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may

or may not be present. Some products may

= Specific Device Code





XX

Μ

SIDE VIEW



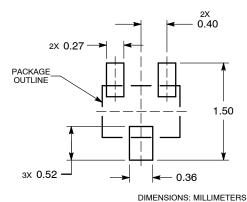
SOT-723 CASE 631AA

DATE 10 AUG 2009

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
Е	0.75	0.80	0.85	
е	0.40 BSC			
ΗE	1.15	1.20	1.25	
Ĺ	0.29 REF			
L2	0.15	0.20	0.25	

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON12989D Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SOT-723		PAGE 1 OF 1		
onsemi and ONSEMi. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.					